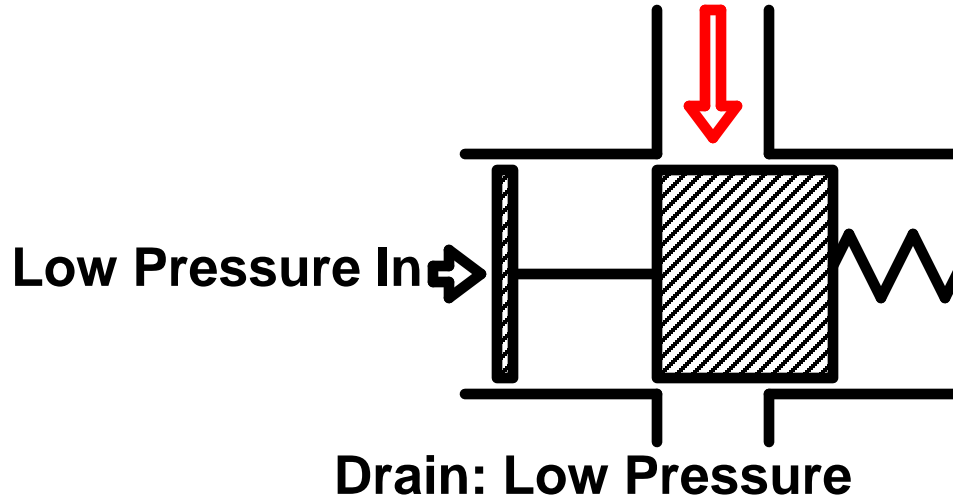
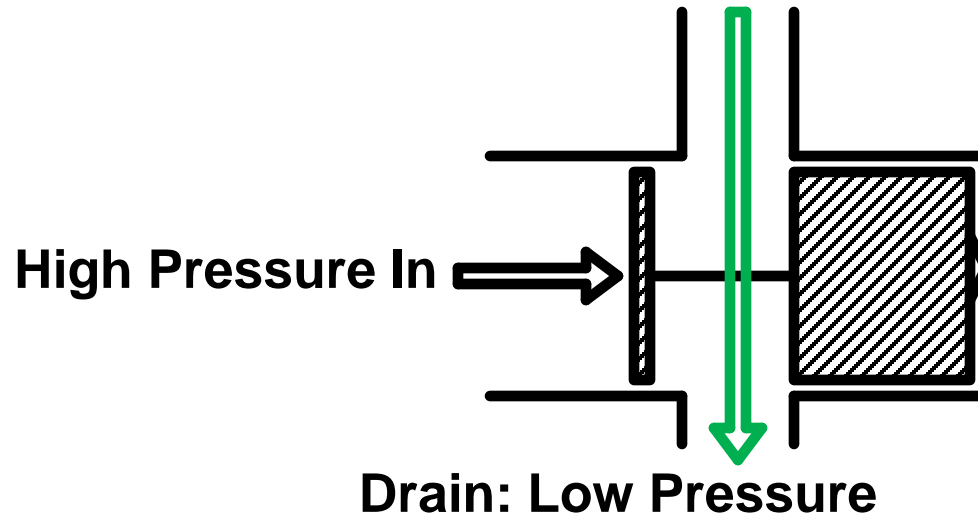


# Pressure Controlled Faucet

Water Tower: High Pressure



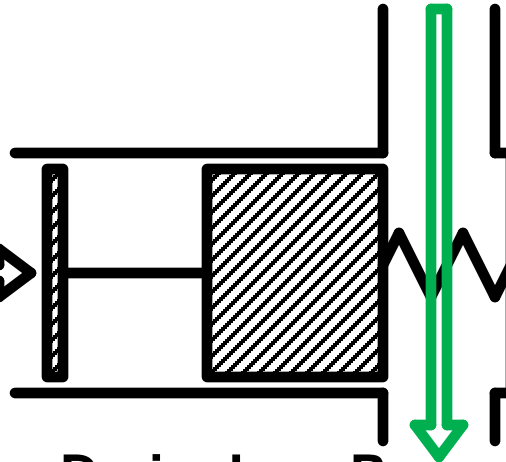
Water Tower: High Pressure



# Opposite behavior: Complementary Device

Water Tower: High Pressure

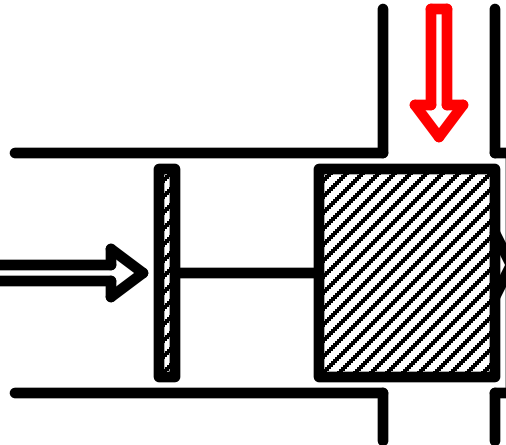
Low Pressure In →



Drain: Low Pressure

Water Tower: High Pressure

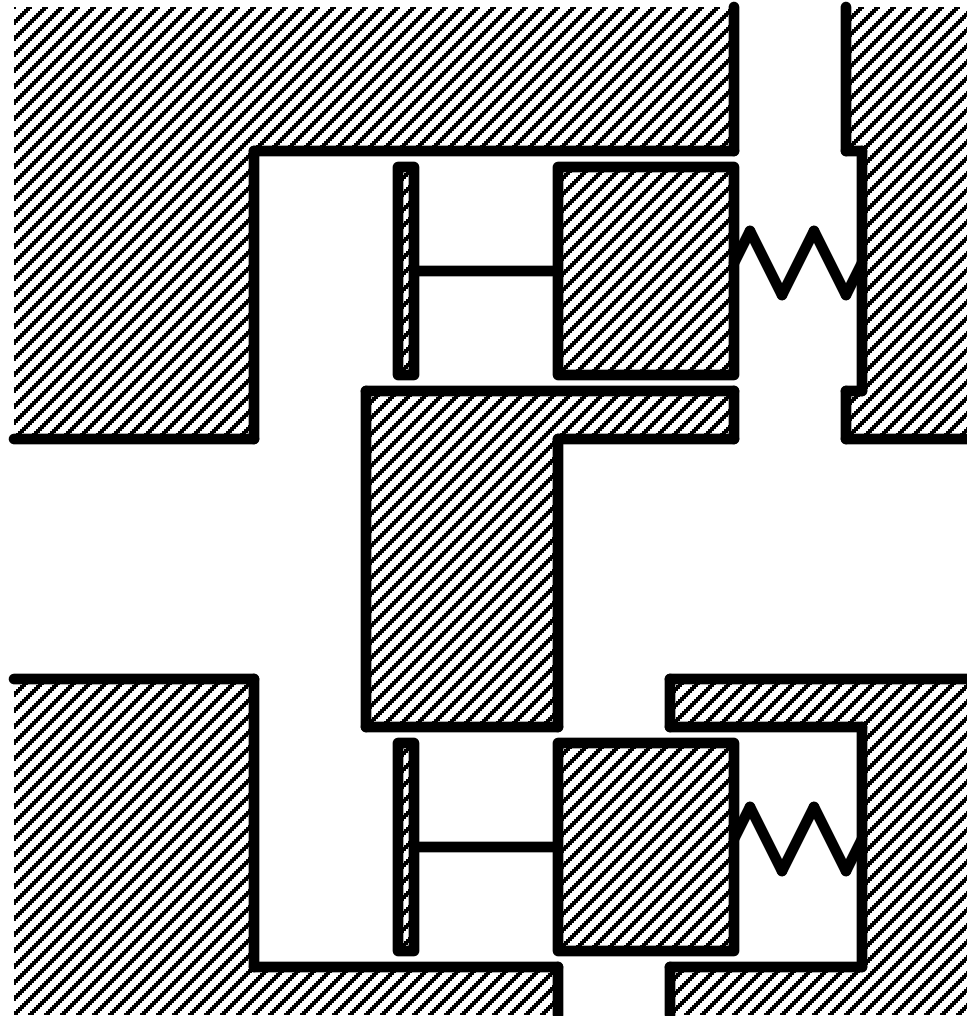
High Pressure In →



Drain: Low Pressure

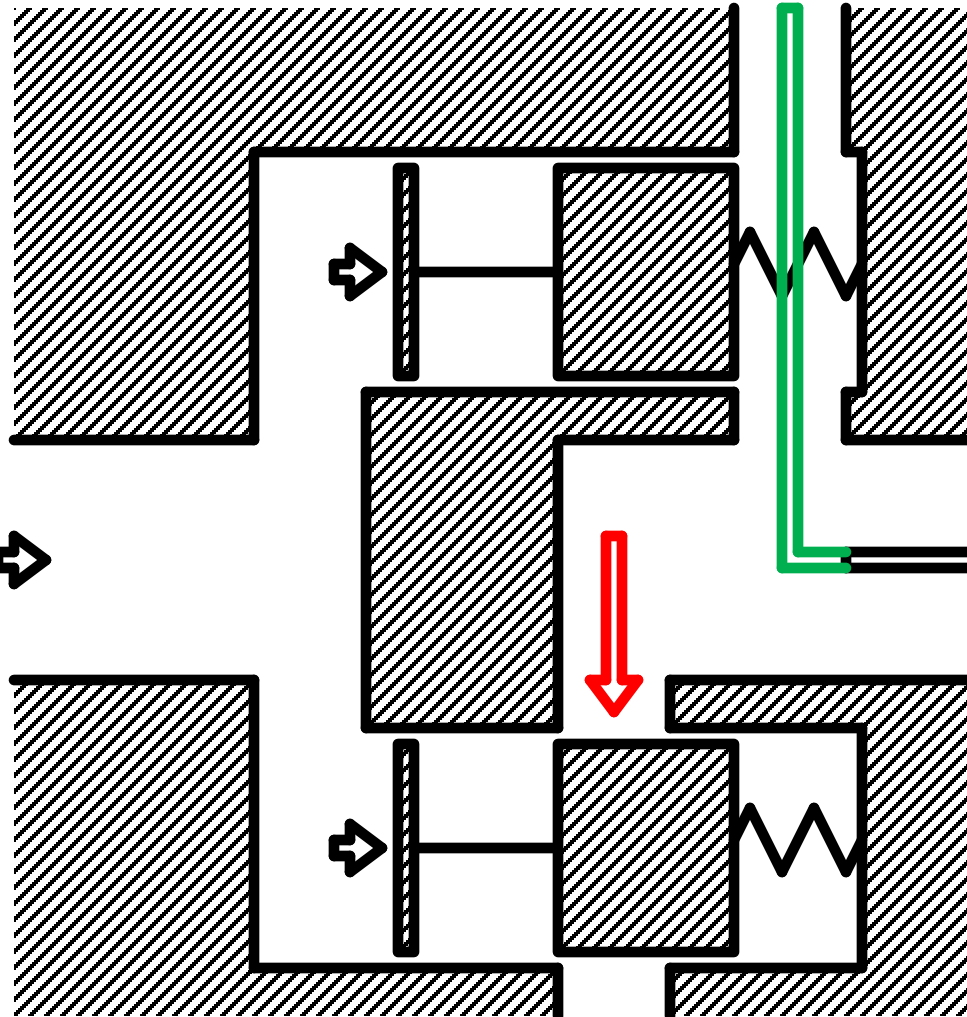
**Let's Build Something. What does it do**

**Water Tower: High Pressure**



**Drain: Low Pressure**

**Water Tower: High Pressure**

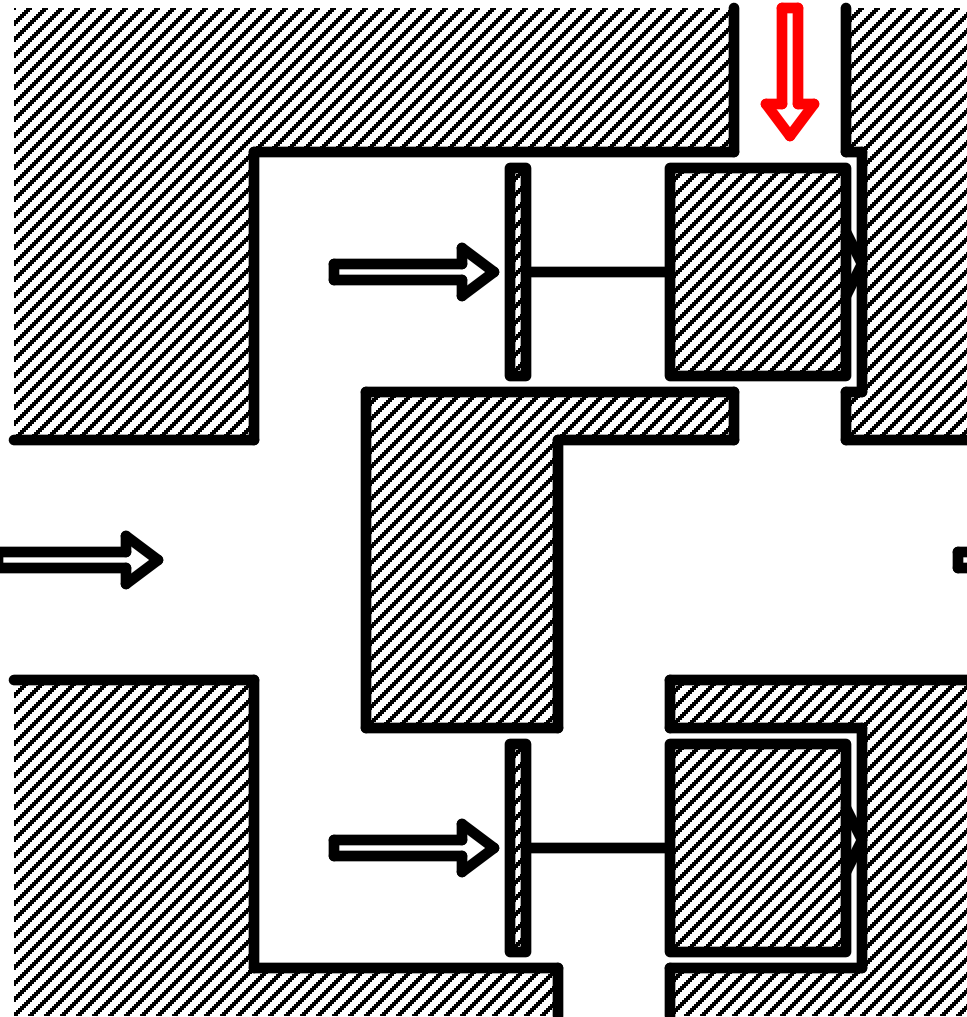


**High Pressure  
Out**

**Drain: Low Pressure**

**Low Pressure In**

**Water Tower: High Pressure**



**High Pressure In**

**Low Pressure Out**

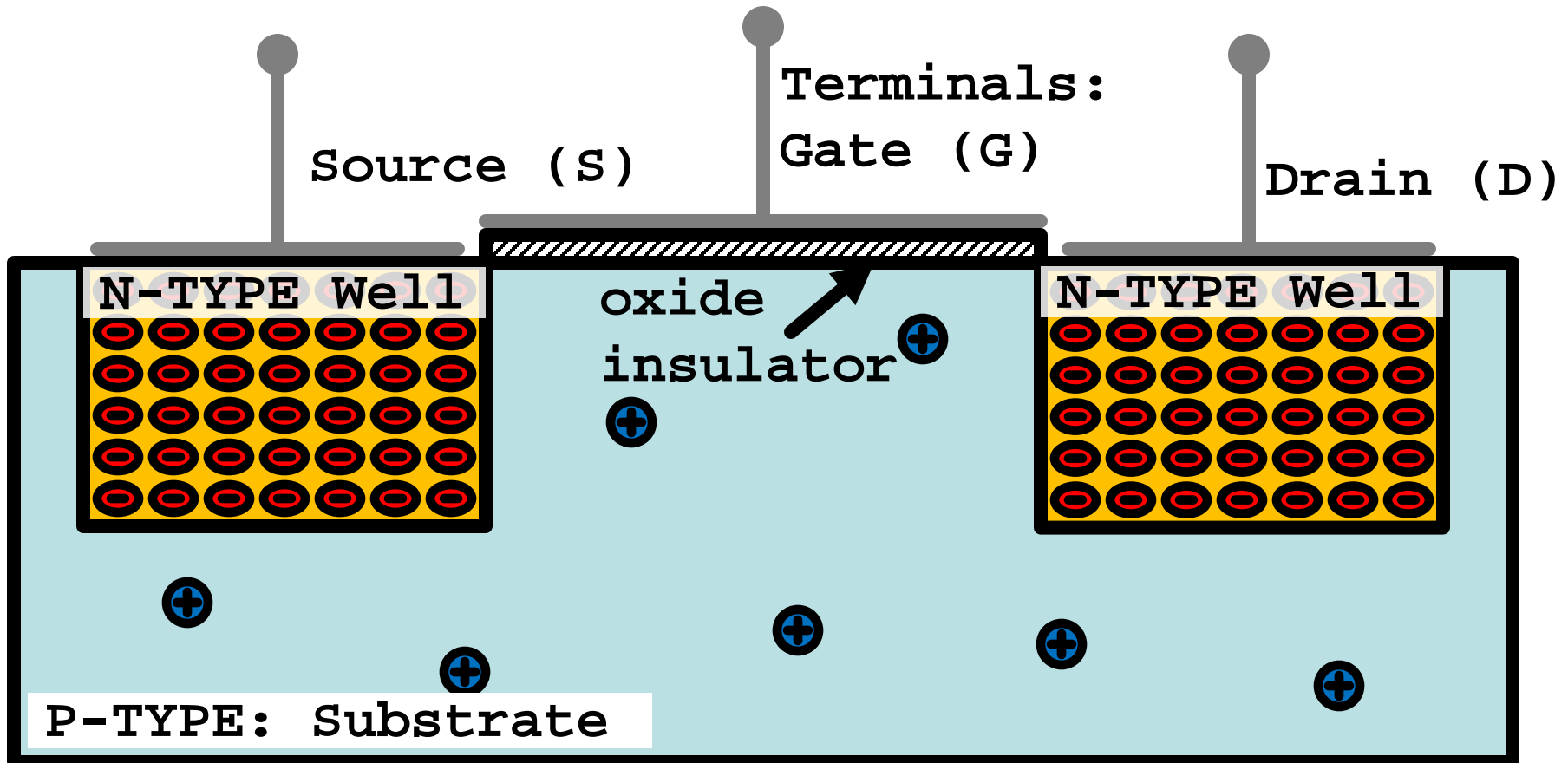
**Drain: Low Pressure**

# MOSFET - Structure

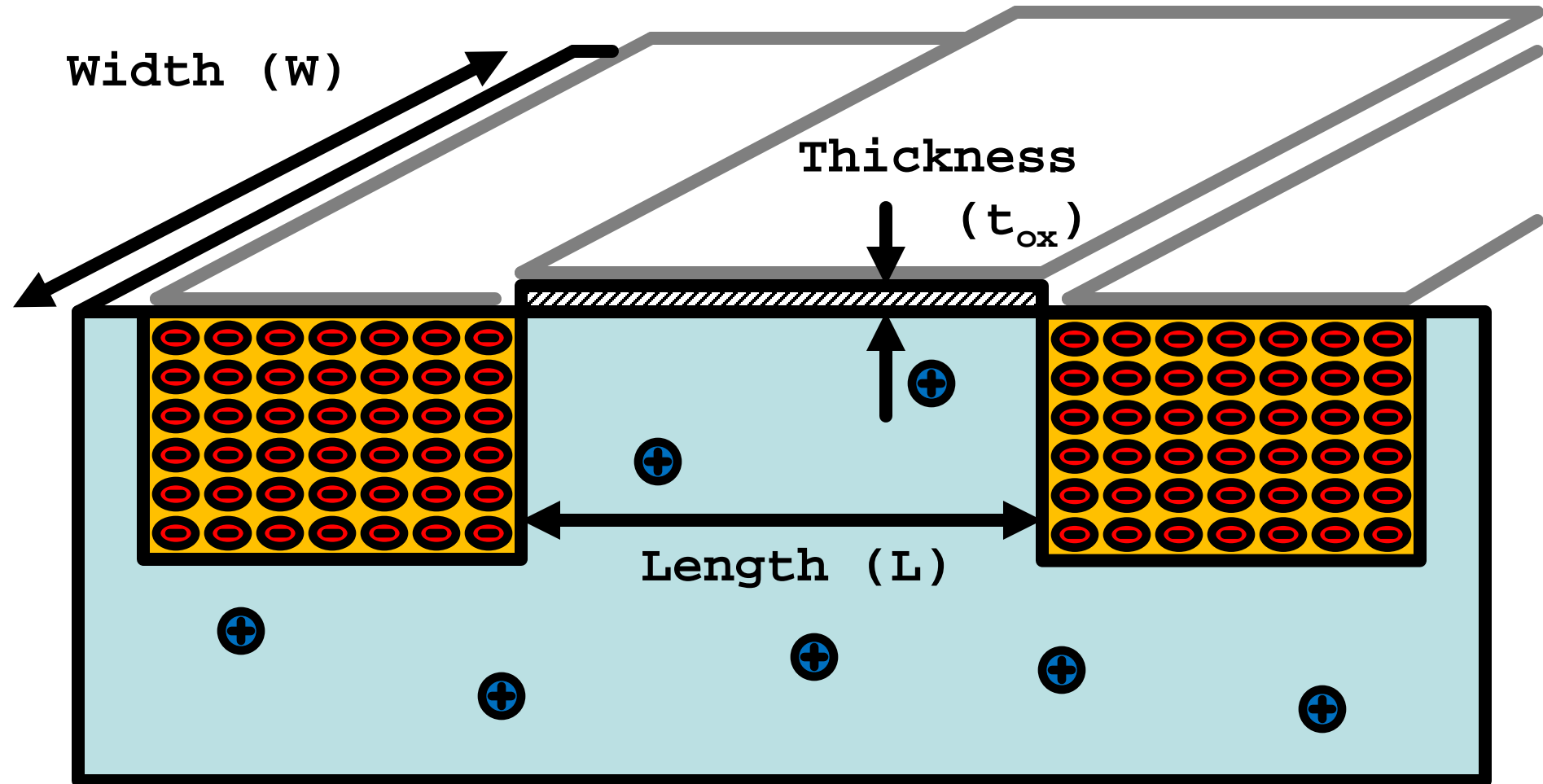
## Properties

Oxide Insulator:  $\epsilon_{\text{ox}} =$

N-Type:  $\mu_n =$



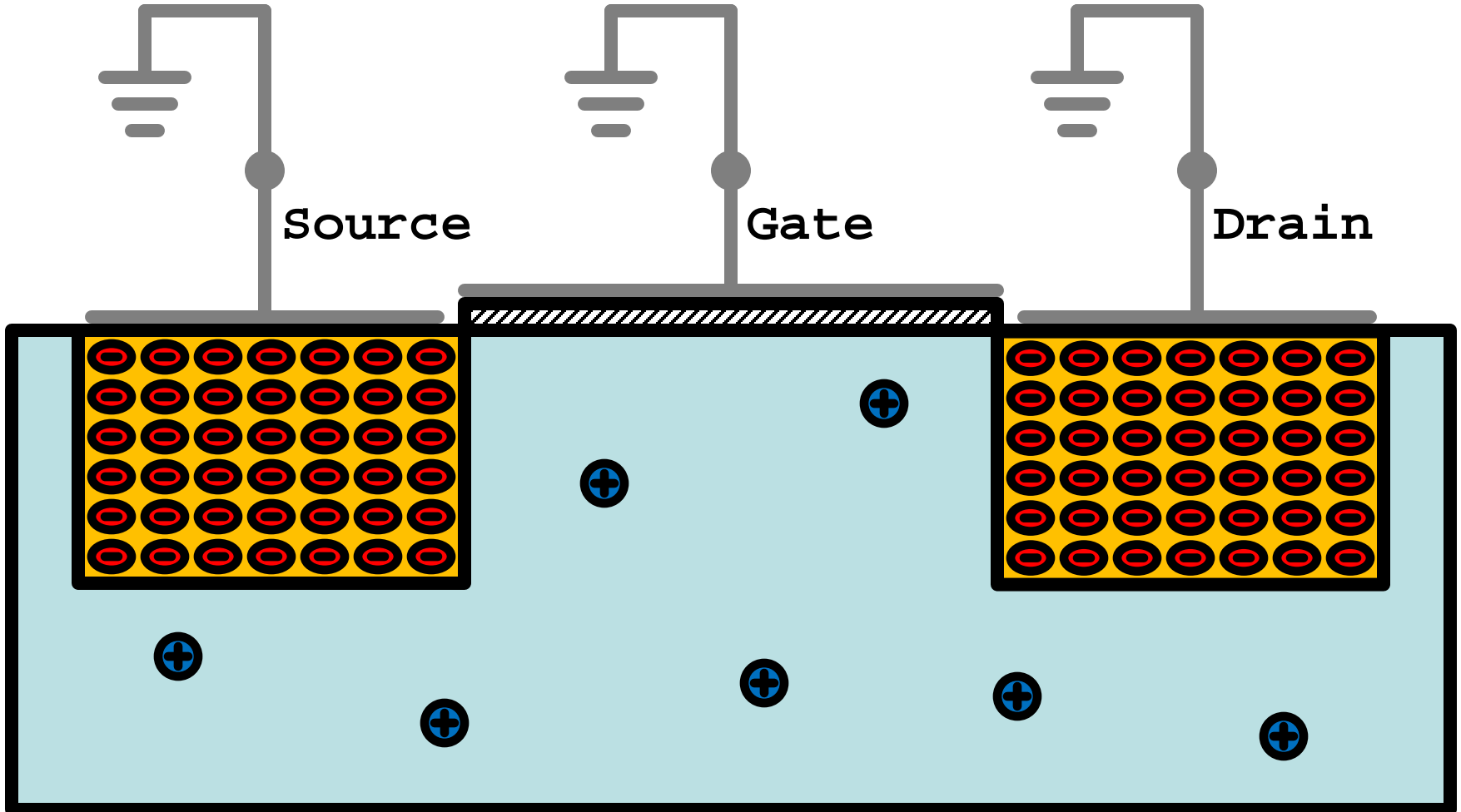
# MOSFET - Dimensions



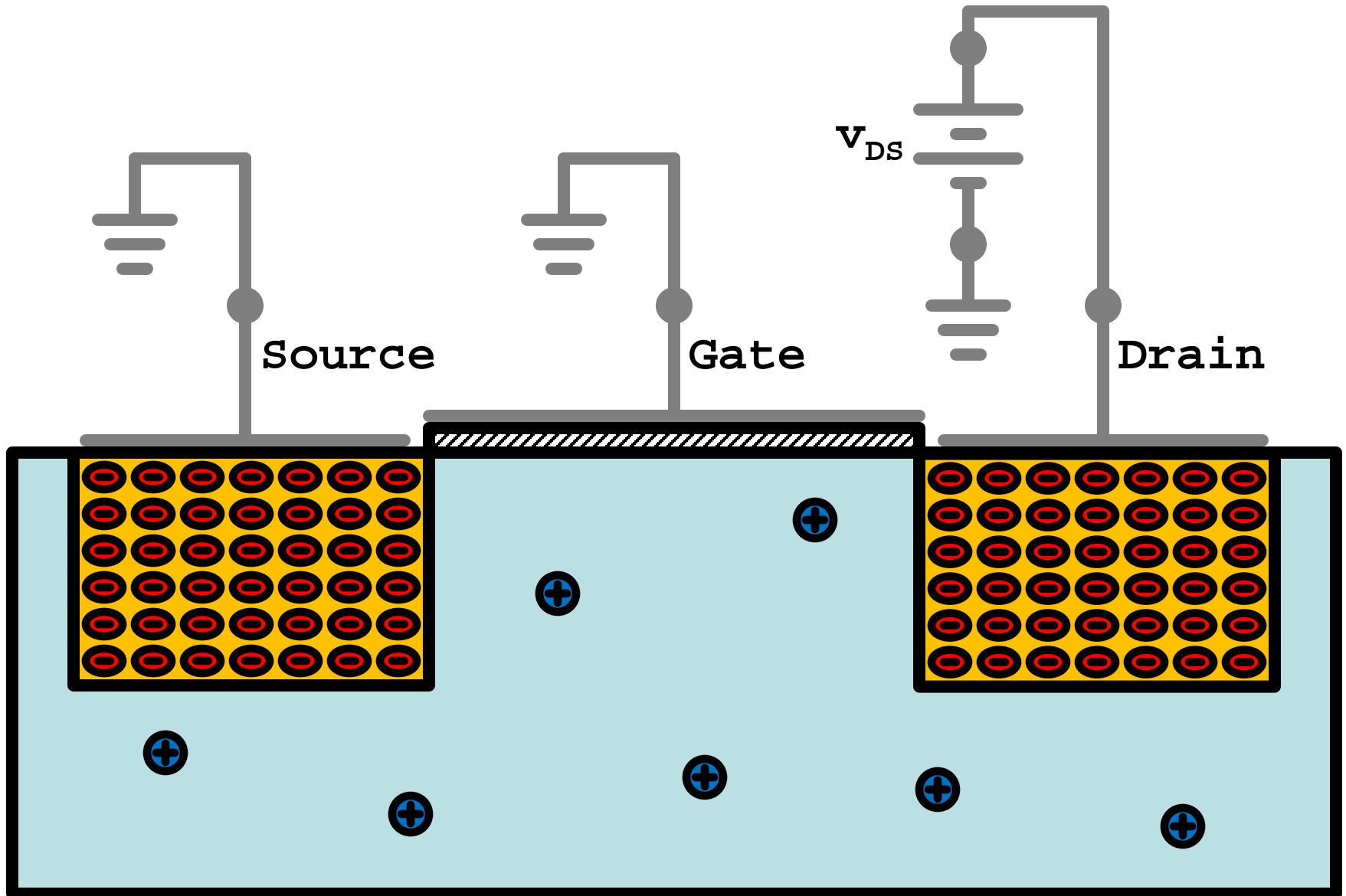
# MOSFET – Operation and Modes

No current flows into the gate.

Try to make current flow into the drain.

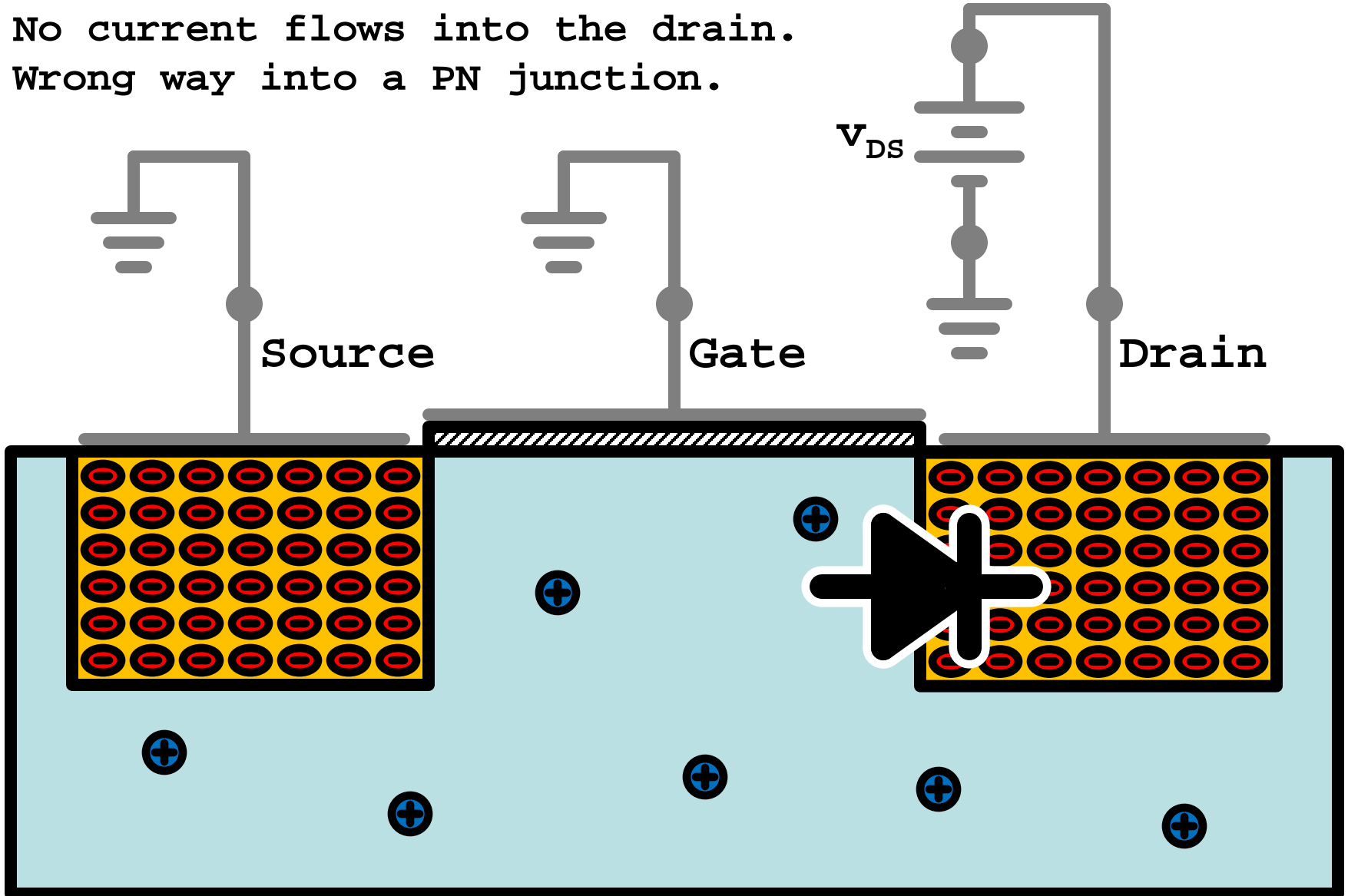


# MOSFET – Operation and Modes

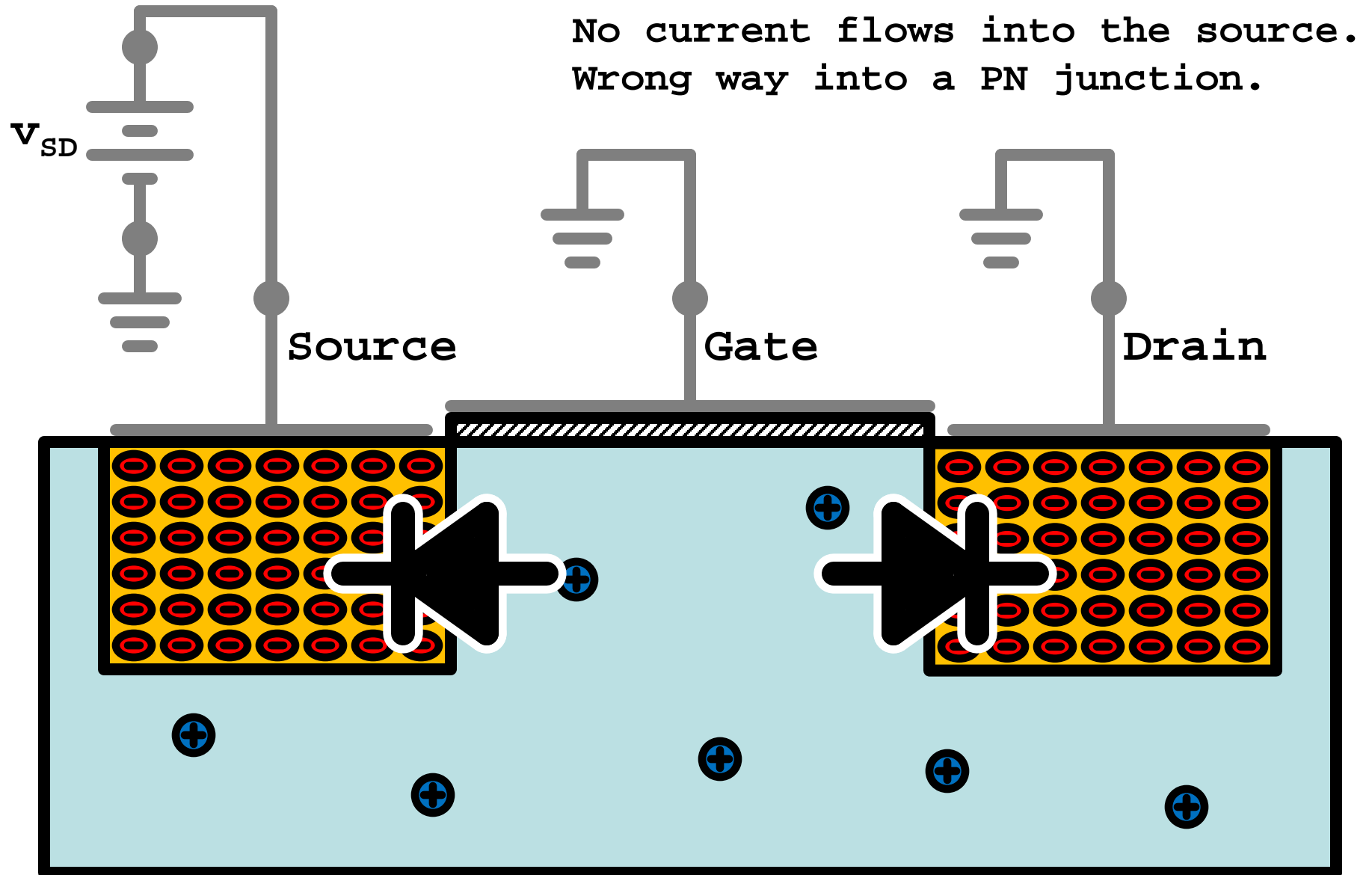


# MOSFET – Operation and Modes

No current flows into the drain.  
Wrong way into a PN junction.

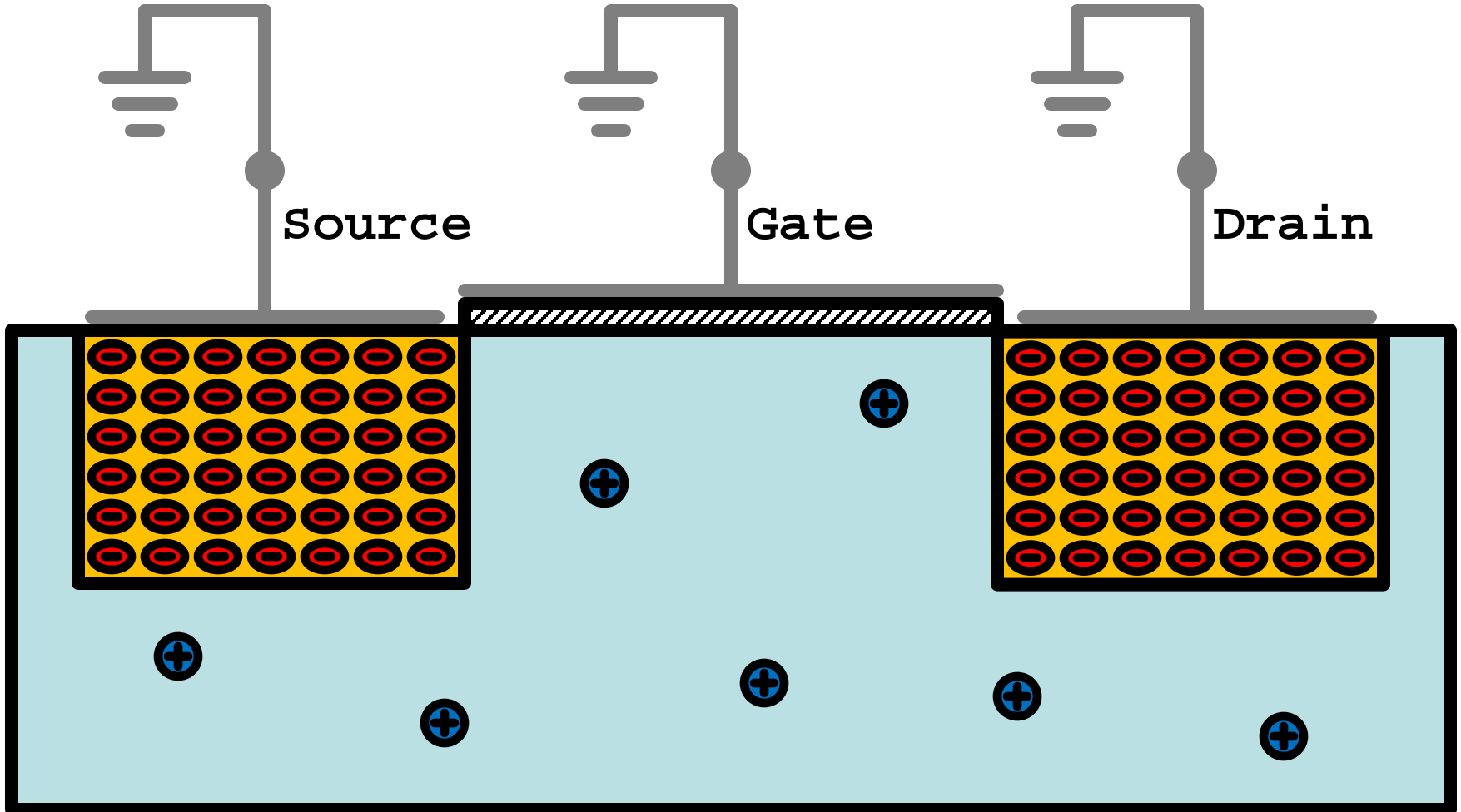


# MOSFET – Operation and Modes



# MOSFET – Operation and Modes

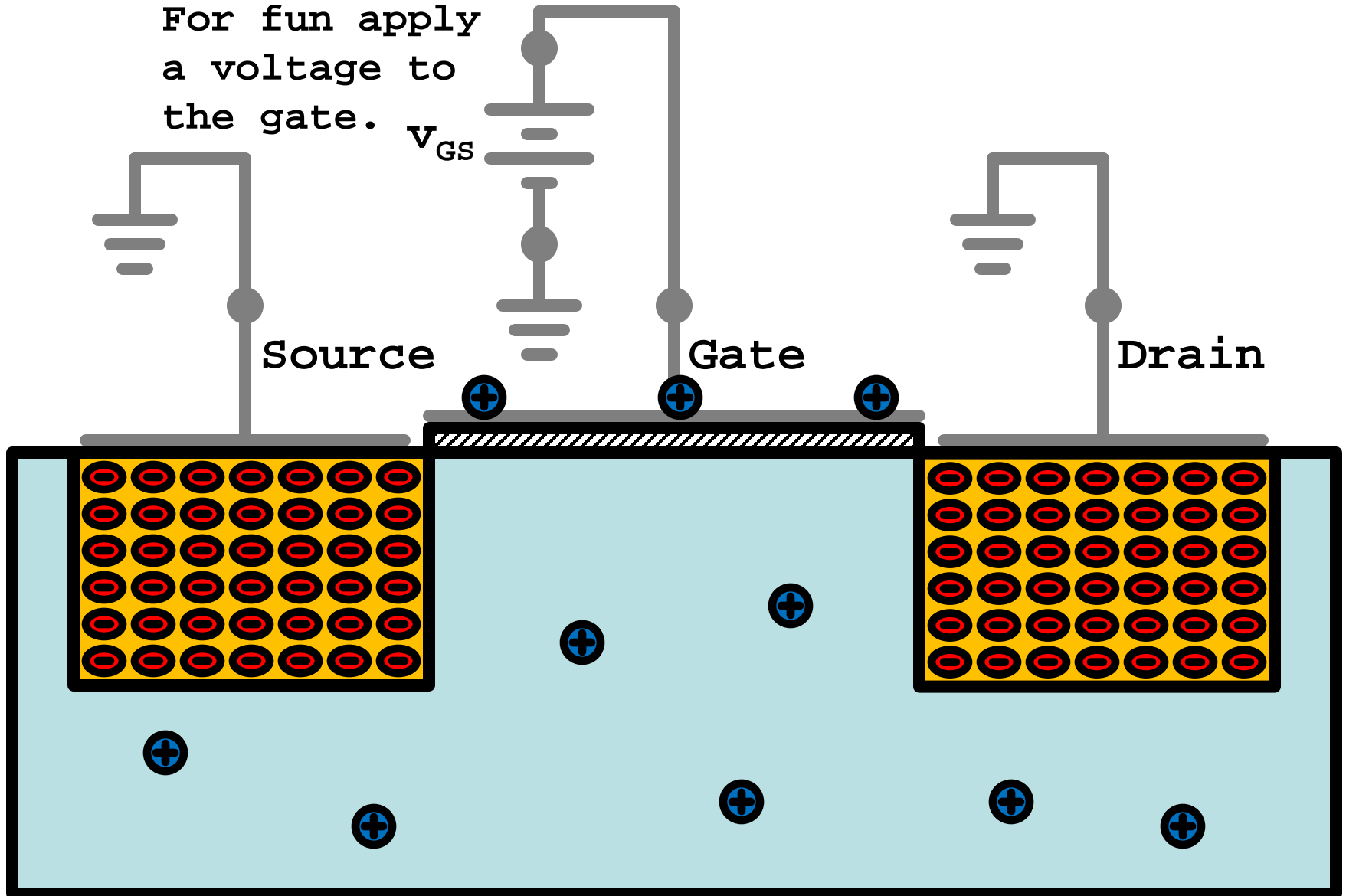
For fun apply a voltage to the gate.



# MOSFET – Operation and Modes

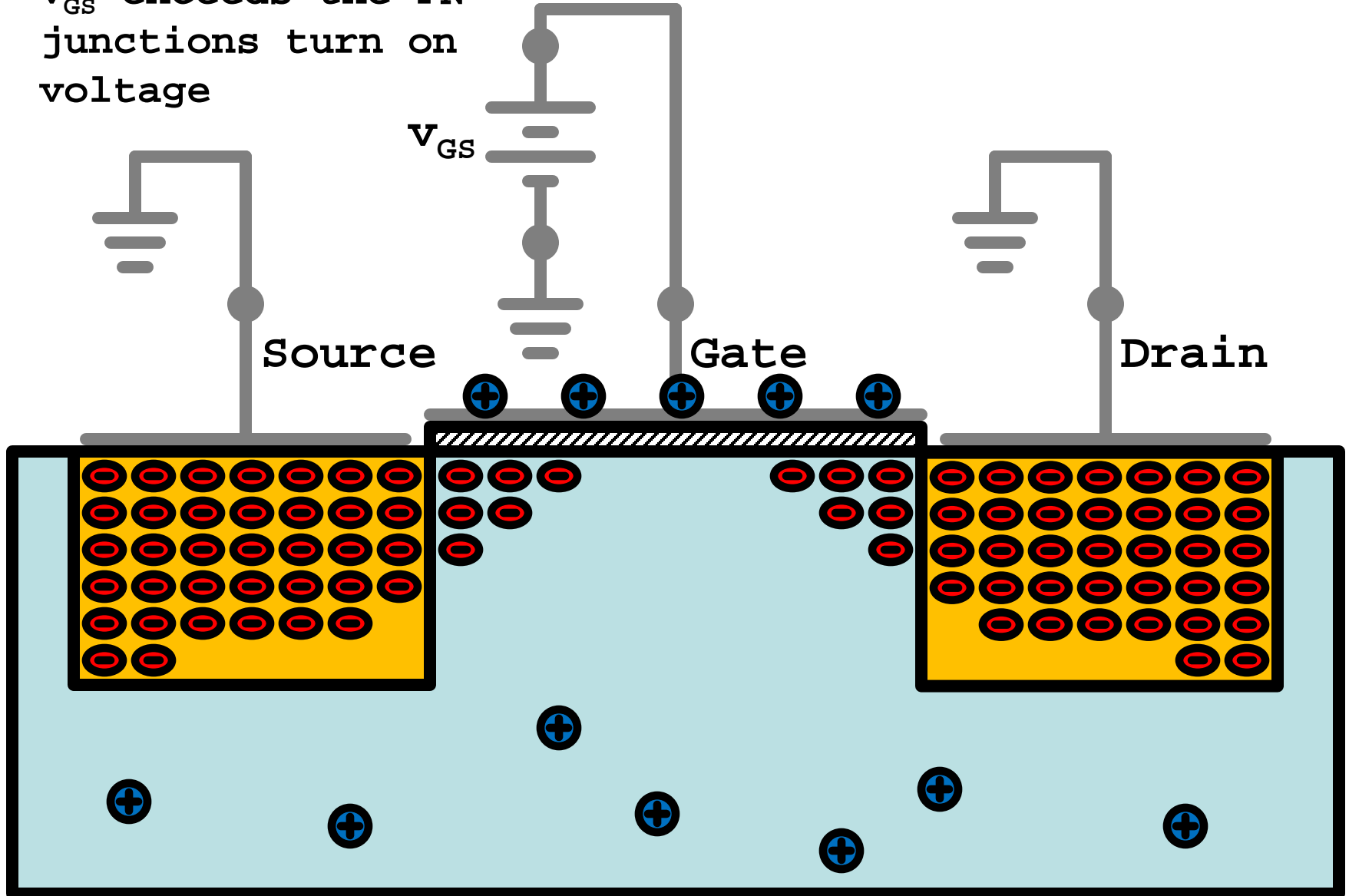
For fun apply  
a voltage to  
the gate.

$V_{GS}$



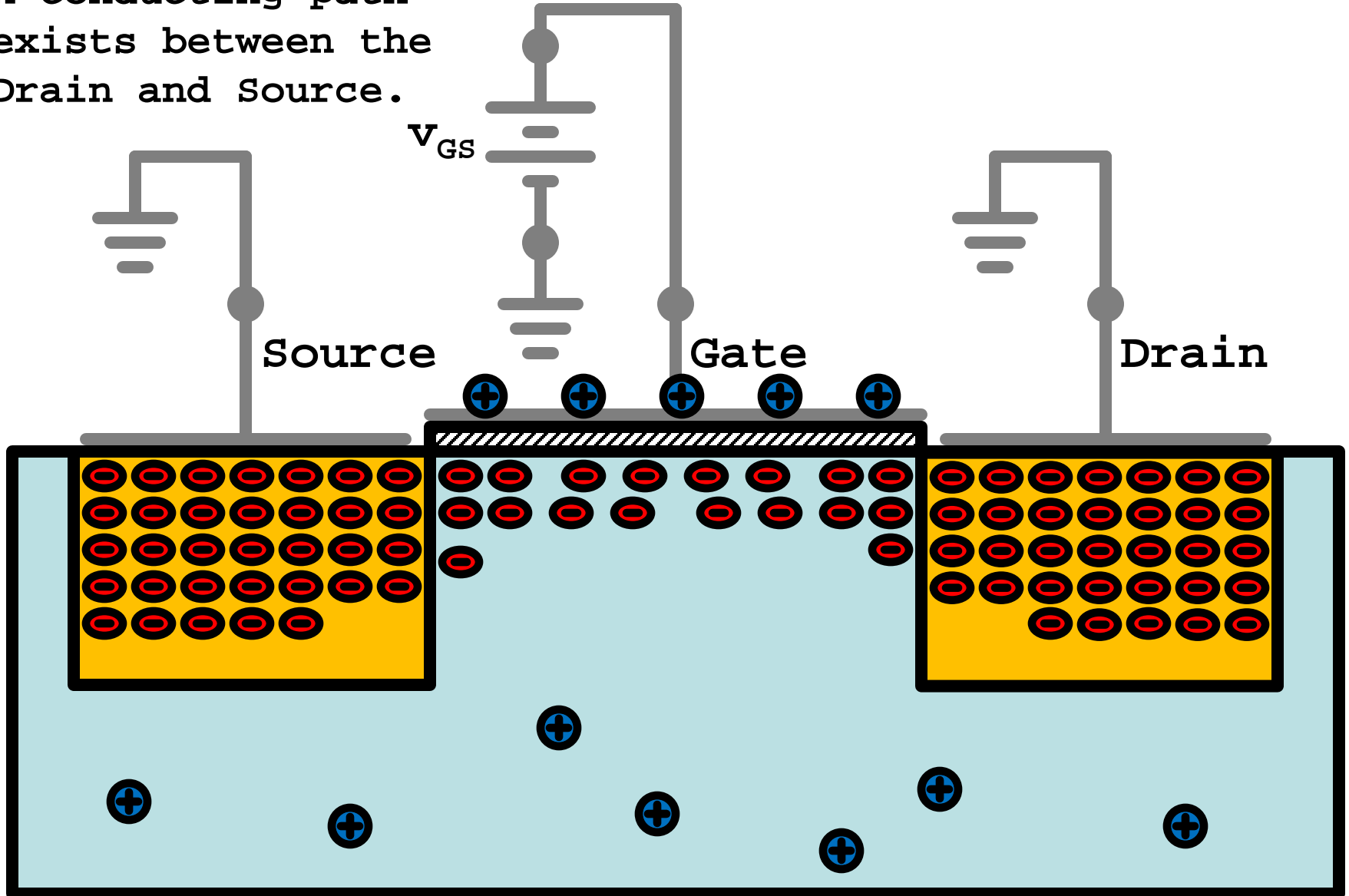
# MOSFET – Operation and Modes

$V_{GS}$  exceeds the PN  
junctions turn on  
voltage

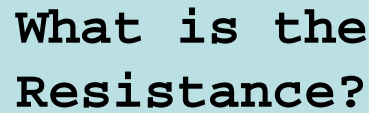


# MOSFET – Operation and Modes

A conducting path exists between the Drain and Source.

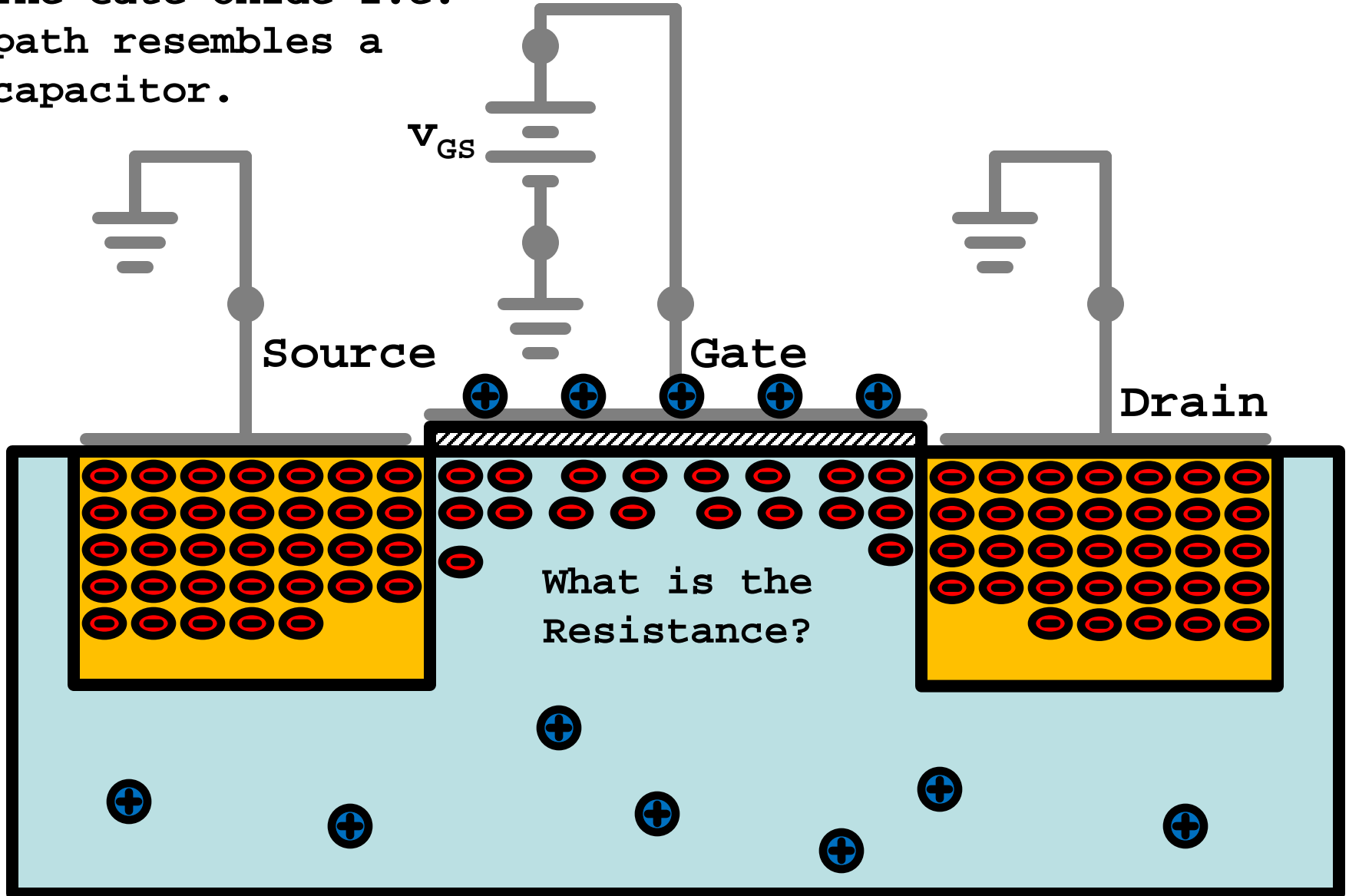


A conducting path exists between the Drain and Source.

 $V_{GS}$ 

# MOSFET – Operation and Modes

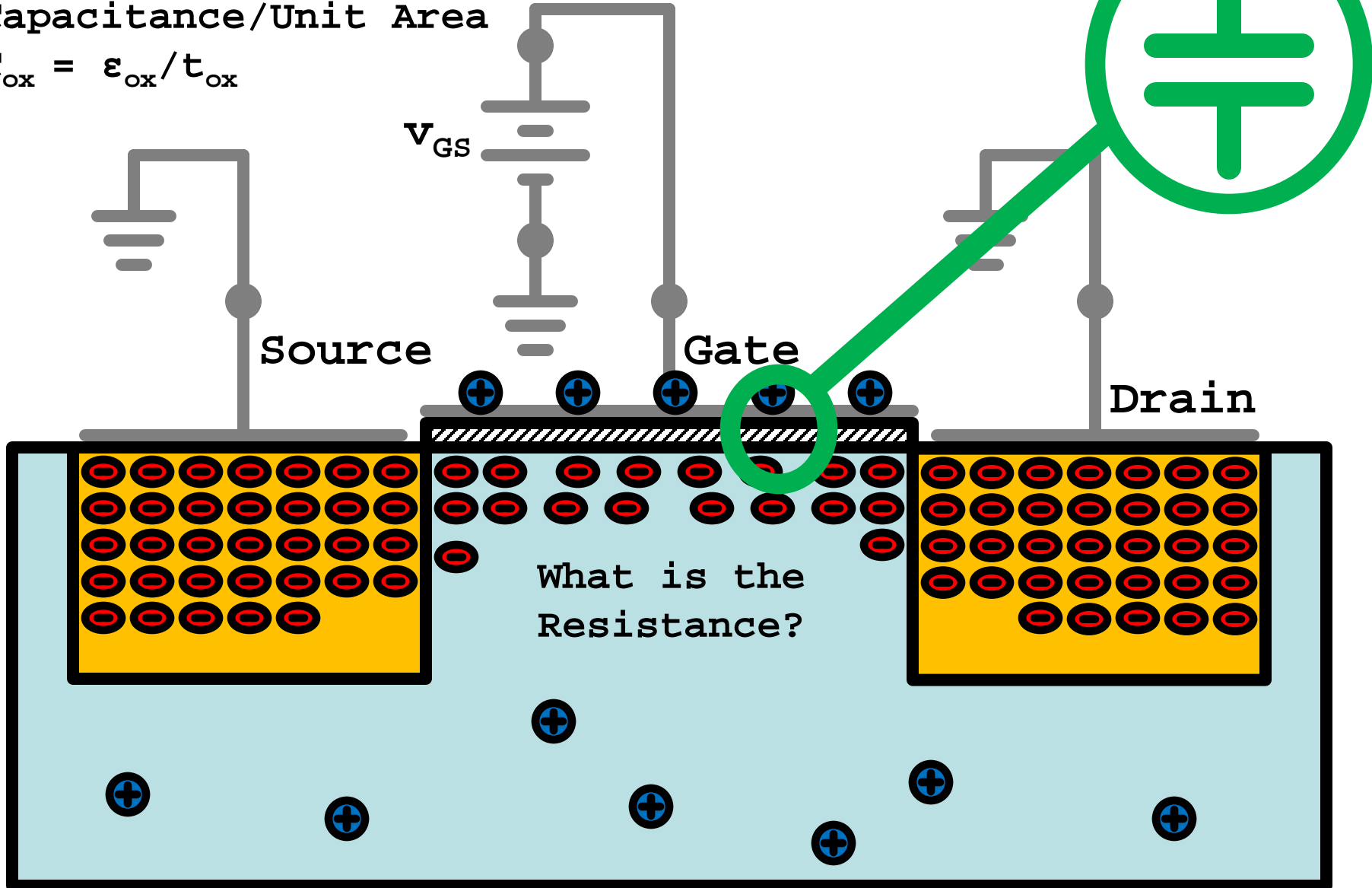
The Gate-Oxide-f.e.  
path resembles a  
capacitor.



# MOSFET – Operation and Modes

Capacitance/Unit Area

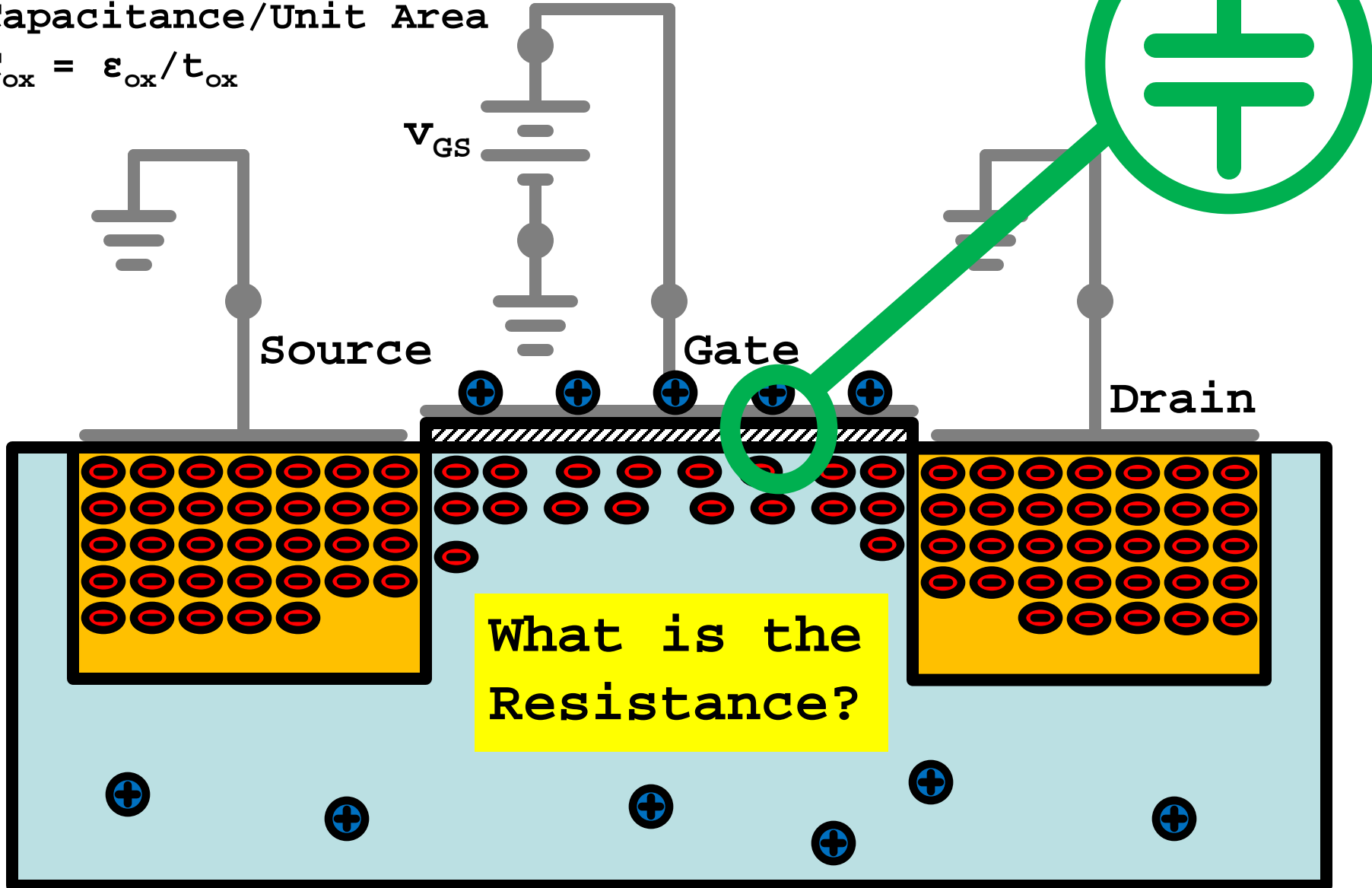
$$C_{\text{ox}} = \epsilon_{\text{ox}} / t_{\text{ox}}$$



# MOSFET – Operation and Modes

Capacitance/Unit Area

$$C_{ox} = \epsilon_{ox} / t_{ox}$$



# Resistance Calculation

$v_{GS}$  exceeds the  
PN junctions turn  
on voltage,  $V_t$ .

Capacitance/Unit Area:  $C_{ox} = \epsilon_{ox}/t_{ox}$

Area =  $W \cdot L$  (from MOSFET Dimensions Slide)

Total Charge ( $Q = C \cdot V$ ):  $Q = (C_{ox} \cdot W \cdot L) \cdot (v_{GS} - V_t)$

Charge/Unit Length =  $Q/L = (C_{ox} \cdot W) \cdot (v_{GS} - V_t)$

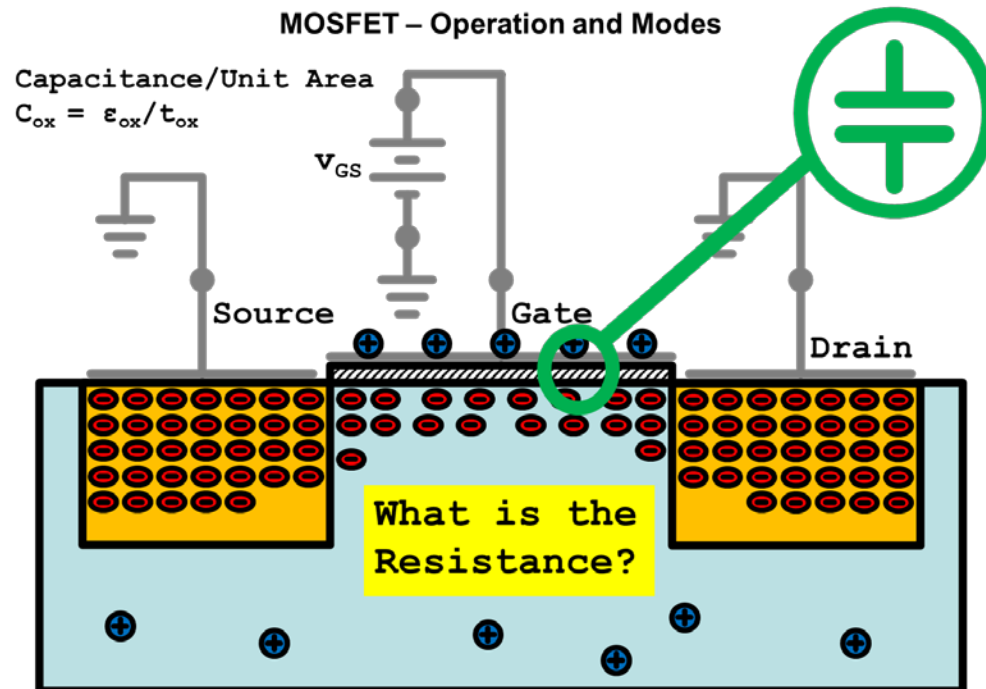
Conductance/Unit Length = mobility  $\cdot$  Charge/Unit Length

Conductance/Unit Length =  $(\mu_n) \cdot (C_{ox} \cdot W) \cdot (v_{GS} - V_t)$

Resistance/Unit Length =  $1 / (\text{Conductance/Unit Length})$

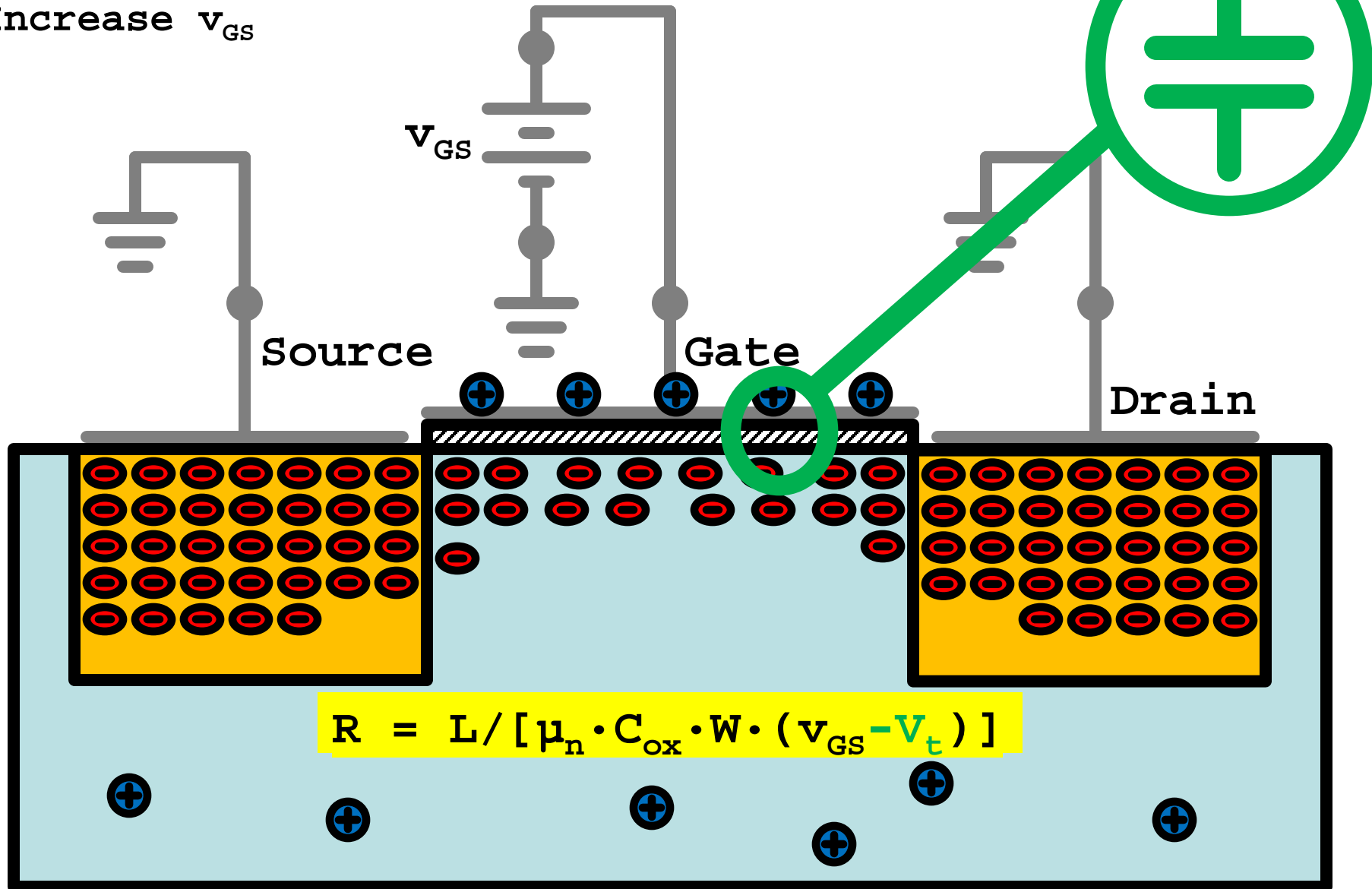
Resistance = Length  $\cdot$  Resistance/Unit Length

$$R = L / [\mu_n \cdot C_{ox} \cdot W \cdot (v_{GS} - V_t)]$$



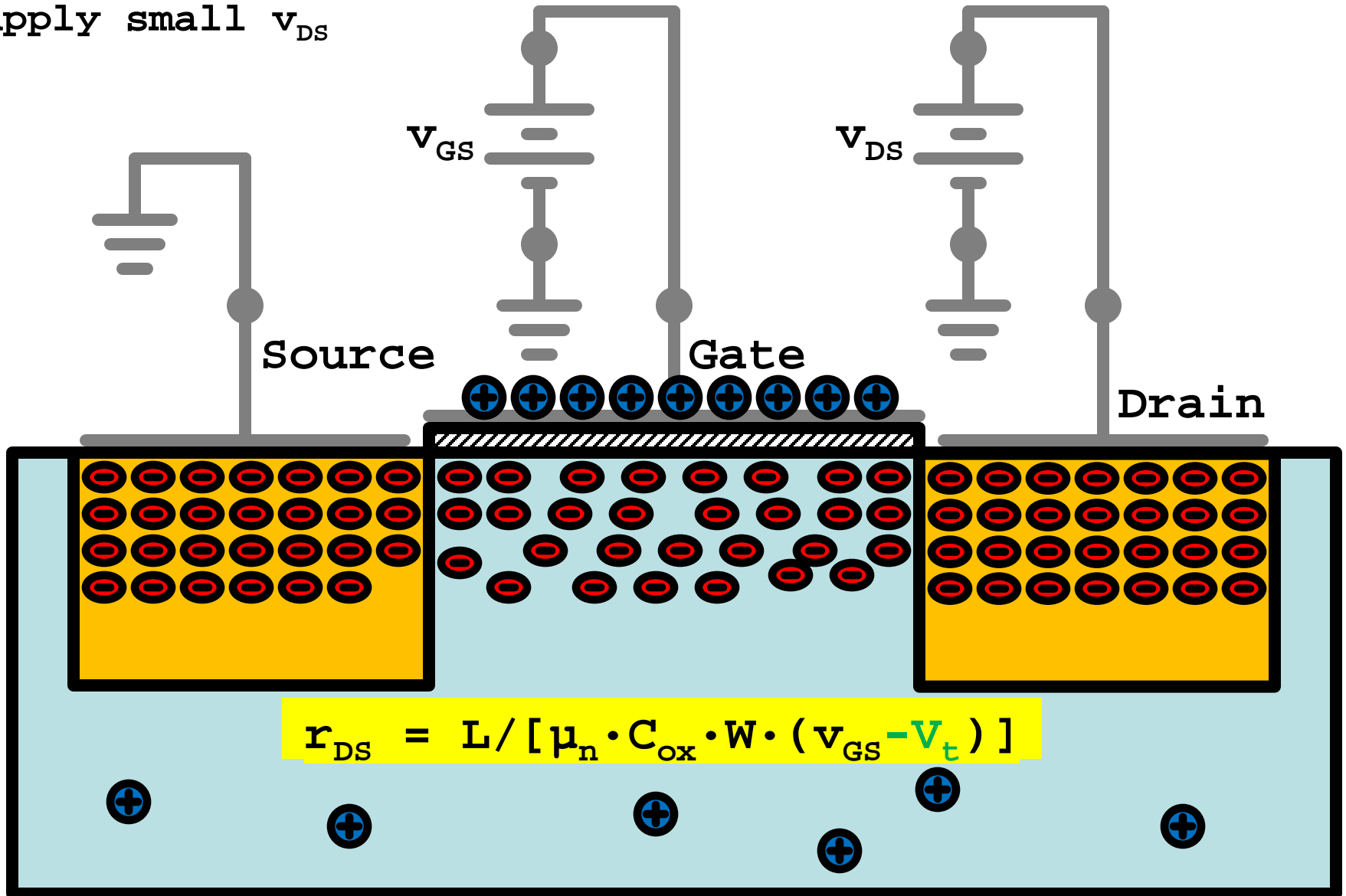
# MOSFET – Operation and Modes

Increase  $v_{GS}$



# MOSFET – Operation and Modes

Apply small  $v_{DS}$



# MOSFET – Operation and Modes

Apply increase  $v_{DS}$   
Current Flows

